



TO-92 Plastic-Encapsulate Transistors

KTC3200 TRANSISTOR (NPN)

FEATURE

Power dissipation

P_{CM} : 0.625 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 0.1 A

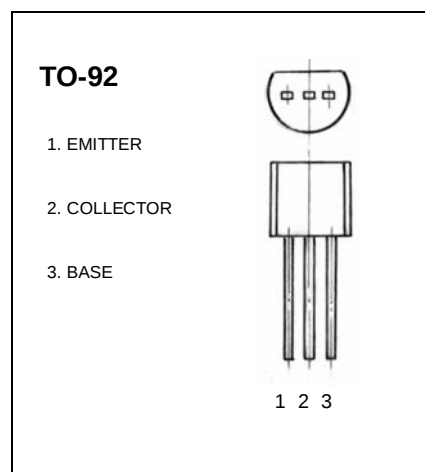
Collector-base voltage

$V_{(BR)CBO}$: 120 V

Operating and storage junction temperature range

T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

T_J : $150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	120			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	120			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=120V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=6V, I_C=2mA$	200		700	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=1mA$			0.3	V
Base-emitter voltage	V_{BE}	$V_{CE}=6V, I_C=2mA$		0.65	0.8	V
Transition frequency	f_T	$V_{CE}=6V, I_C=1mA$ $F=30MHz$		100		MHz

CLASSIFICATION OF h_{FE}

Rank	GR	BL
Range	200-400	350-700

